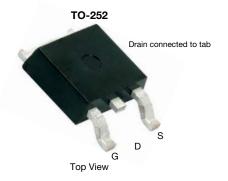


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Automotive N-Channel 60 V (D-S) 175 °C MOSFET

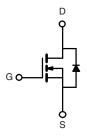
PRODUCT SUMMARY d					
V _{DS} (V)	60				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.042				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.060				
I _D (A)	15				
Configuration	Single				
Package	TO-252				



FEATURES

- TrenchFET® power MOSFET
- 100 % R_g and UIS tested
- AEC-Q101 qualified
- Package with low thermal resistance
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





N-Channel MOSFET

ABSOLUTE MAXIMUM RA	TINGS (T _C = 25	5 °C, unless otherwise	e noted)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	60	V	
Gate-Source Voltage		V _{GS}	± 20	T v	
Continuous Drain Current	T _C = 25 °C ^a		15		
Continuous Drain Current	T _C = 125 °C	l _D	10		
Continuous Source Current (Diode Conduction) ^a		Is	15	A	
Pulsed Drain Current ^b		I _{DM}	50		
Single Pulse Avalanche Current		I _{AS}	18		
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	16.2	mJ	
Maximum Power Dissipation b	T _C = 25 °C	В	37	W	
waxiiiuiii Fowei Dissipation -	T _C = 125 °C	P _D	11]	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	SYMBOL LIMIT		
Junction-to-Ambient PCB Mount c		R_{thJA}	50	°C/W	
Junction-to-Case (Drain)		R _{thJC}	4	G/W	

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).

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PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT	
Static				I.			
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} =	= 0 V, I _D = 250 μA	60	-	-	.,
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	: V _{GS} , I _D = 250 μA	1.5	2	2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
		V _{GS} = 0 V	V _{DS} = 60 V	-	-	. 1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μA
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α
		V _{GS} = 10 V	I _D = 10 A	-	0.036	0.042	Ω
		V _{GS} = 10 V	I _D = 10 A, T _J = 125 °C	-	-	0.075	
Dunin Course On Chata Basistanas 8		V _{GS} = 10 V	I _D = 10 A, T _J = 175 °C	-	-	0.090	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V	I _D = 10 A, T _J = 125 °C	-	0.092	-	
		V _{GS} = 4.5 V	I _D = 10 A, T _J = 175 °C	-	0.110	-	
		V _{GS} = 4.5 V	I _D = 10 A	-	0.048	0.060	
Forward Transconductance b	9 _{fs}	V _{DS} = 15 V, I _D = 6 A		-	11	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			=.	425	535	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	=	95	120	pF
Reverse Transfer Capacitance	C _{rss}			-	40	50	
Total Gate Charge ^c	Qg			=.	9.5	15	
Gate-Source Charge c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 30 \text{ V}, I_{D} = 15 \text{ A}$	=	1.7	-	nC
Gate-Drain Charge ^c	Q _{gd}				2.5	=.	1
Gate Resistance	R_g	f = 1 MHz		1.2	2.5	5.4	Ω
Turn-On Delay Time ^c	t _{d(on)}	$V_{DD} = 30 \text{ V, } R_L = 2 \Omega$ $I_D \cong 15 \text{ A, } V_{GEN} = 10 \text{ V, } R_g = 1 \Omega$		-	5	8	- ns
Rise Time ^c	t _r			-	10	15	
Turn-Off Delay Time ^c	t _{d(off)}			-	13	20	
Fall Time ^c	t _f			-	8	12	
Source-Drain Diode Ratings and Chara	cteristics b						
Pulsed Current ^a	I _{SM}			-	-	50	Α
Forward Voltage	V _{SD}	I _F =	10 A, V _{GS} = 0 V	-	0.9	1.2	V
Reverse Recovery Time	t _{rr}	I _F = 15 A, dl/dt = 100 A/μs		-	29	60	ns

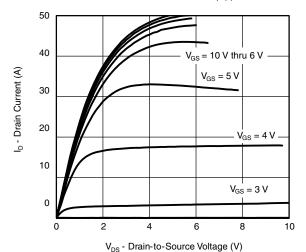
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

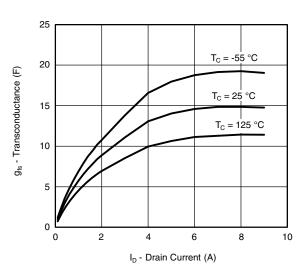
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



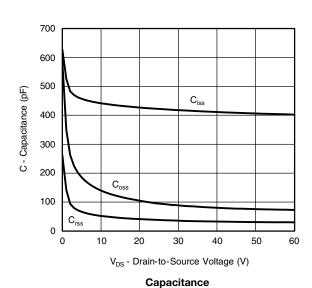
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

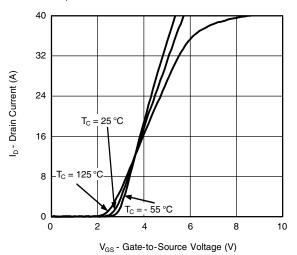


Output Characteristics

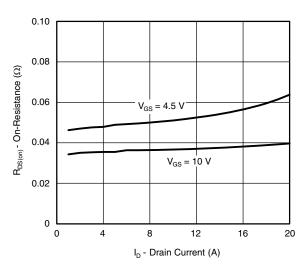


Transconductance

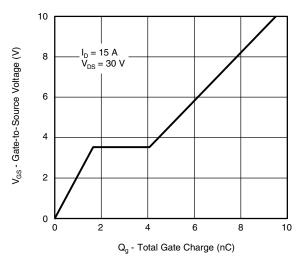




Transfer Characteristics



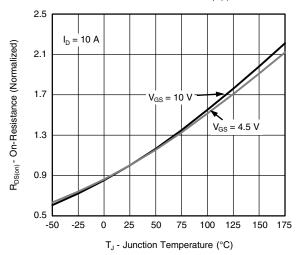
On-Resistance vs. Drain Current

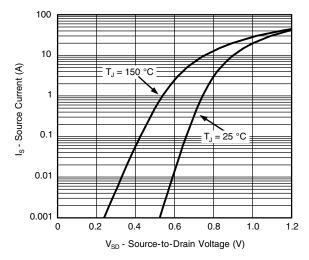


Gate Charge

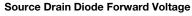


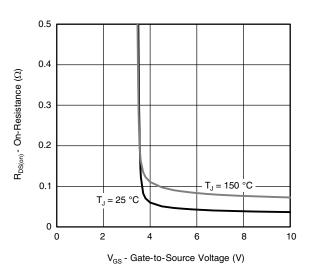
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

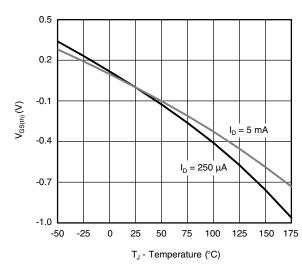




On-Resistance vs. Junction Temperature

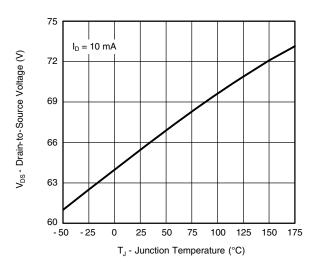






On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

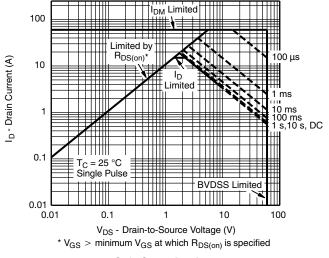


On-Resistance vs. Junction Temperature

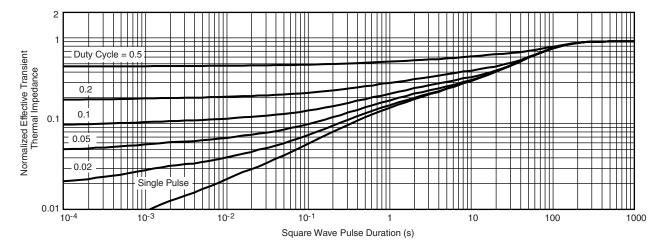
For technical questions, contact: automostech



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



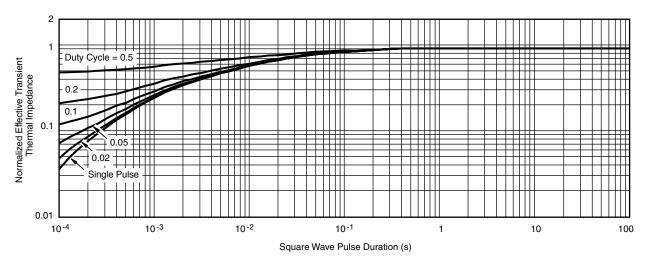
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg268880.



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REVISION	HISTORY a	
REVISION	DATE	DESCRIPTION OF CHANGE
G	04-Aug-15	Revised R _g minimum limit

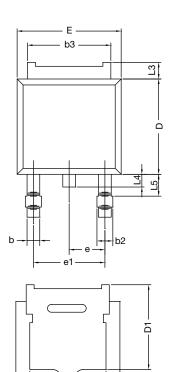
Note

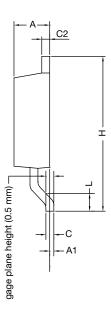
a. As of April 2014



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TO-252AA Case Outline





	MILLIMETERS		INCHES		
DIM.	MIN.	MAX.	MIN. MAX.		
Α	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090 BSC		
e1	4.56	BSC	0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T13-0592-Rev. A, 02-Sep-13					

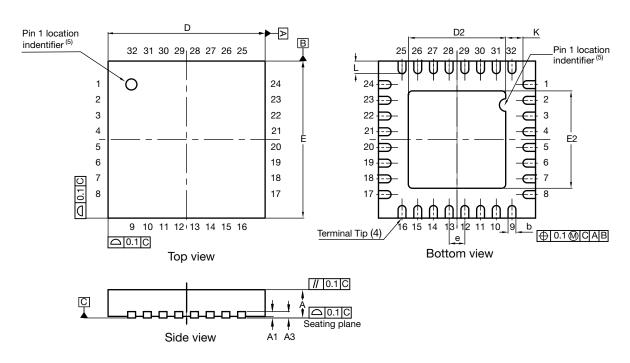
DWG: 6019

Note

• Dimension L3 is for reference only.

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QFN32 5 x 5 Case Outline



DIM.	MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	0.75	0.85	0.95	0.029	0.033	0.037	
A1	0.00	-	0.05	0.000	-	0.002	
A3		0.20 ref.		0.008 ref.			
b	0.18	0.25	0.30	0.007	0.010	0.012	
D		5.00 BSC			0.197 BSC		
D2	3.00	3.10	3.20	0.118	0.122	0.126	
е		0.50 BSC			0.020 BSC		
E		5.00 BSC			0.197 BSC		
E2	3.00	3.10	3.20	0.118	0.122	0.126	
K	0.20	-	-	0.008	-	-	
L	0.30	0.40	0.50	0.012	0.016	0.020	
N (3)	32				32		
Nd ⁽³⁾	8			8			
Ne ⁽³⁾	8				8		

- (1) Use millimeters as the primary measurement
- (2) Dimensioning and tolerances conform to ASME Y14.5M. 1994
- N is the number of terminals,
 - Nd is the number of terminals in X-direction and
 - Ne is the number of terminals in Y-direction.
- (4) Dimension b applies to plated terminal and is measured between 0.15 mm and 0.30 mm from terminal tip
- (5) The pin #1 identifier must be existed on the top surface of the package by using indentation mark or other feature of package body
- Package warpage max. 0.05 mm

S14-2079-Rev. A, 20-Oct-14

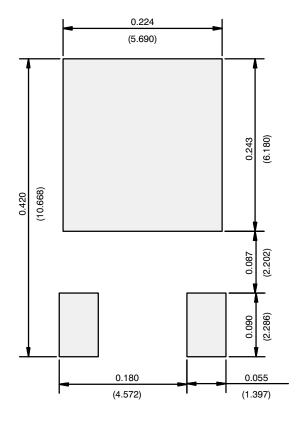
DWG: 6027

Revision: 20-Oct-14

Document Number: 67244



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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